

Substitute for form 1449A/PTO

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of

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Application Number

09/020.565

Filing Date

January 16, 1998

First Named Inventor

Joseph W. Lyding et al.

Group Art Unit

1763

Examiner Name

Unknown

Attorney Docket Number

22010-128/IL-2-CON

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Subclass

Examiner Initials*	Cite No.¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code² (if known)			
La		3,849,204		Fowler	11/19/1974	
		3,923,559		Sinha	12/02/1975	
		4,113,514		Pankove et al.	09/12/1978	
		4,151,007		Levinstein et al.	04/24/1979	
		4,290,825		Dearnaley et al.	09/22/1981	
		4,334,486		Chenevas-Paule et al.	05/25/1982	
		4,620,211		Baliga et al.	10/28/1986	
		5,059,551		Chevallier et al.	10/22/1991	
Su		5,248,348		Miyachi et al.	09/28/1993	
		5,250,446		Osawa et al.	10/05/1993	
		5,264,724		Brown et al.	11/23/1993	

FOREIGN PATENT DOCUMENTS

[illegible]

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Khai Minh Lee

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Substitute for form 1449B/PTO

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Sheet

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of

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Complete if Known

Application Number	09/020,565
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Lee		GANGULY, Gautam and MATSUDA, Akihisa, "Light-Induced Defect Densities in Hydrogenated and Deuterated Amorphous Silicon Deposited at Different Substrate Temperatures", <u>The Amer. Physical Soc.</u> , Vol. 49, No. 16, pp. 10-986-10 990, (April 15, 1994).	
Lee		MIKKELSEN, J.C., Jr., "Secondary Ion Mass Spectrometry Characterization of D ₂ O and H ₂ ¹⁸ O Steam Oxidation of Silicon", <u>J. of Electronic Mat'l's</u> , Vol. 11, No. 3, pp. 541-558, (1982).	
Lee		MYERS, S.M. and RICHARDS, P.M., "Interactions of Deuterium With Ion-Irradiated SiO ₂ on Si", <u>J. Appl. Phys.</u> , Vol. 67, No. 9, pp. 4064-4071 (May 1, 1990).	
Lee		PARK, Heungsoo and HELMS, C.R., "The Effect of Annealing Treatment on the Distribution of Deuterium in Silicon and in Silicon/Silicon Oxide Systems", <u>J. Electrochem. Soc.</u> , Vol. 139, No. 7, pp. 2042-2046 (July 1992).	
Lee		SAKS, N.S. and RENDELL, R.W., "The Time-Dependence of Post-Irradiation Interface Trap Build-up in Deuterium-Annealed Oxides", <u>IEEE Transactions on Nuclear Science</u> , Vol. 39, No. 6, pp. 2220-2229 (December 1992).	
Lee		SAKS, N.S. and RENDELL, R.W., "Time-Dependence of the Interface Trap Build-up in Deuterium-Annealed Oxides After Irradiation", <u>Appl. Phys. Lett.</u> , Vol. 61, No. 25, pp. 3014-3016 (December 21, 1992).	
Lee		ZAVADA, J.M., WEISS, B.L., BRADLEY, I.V., THEYS, B., CHEVALLIER, J., RAHBI, R., ADDINALL, R., NEWMAN, R.C. and JENKINSON, H.A., "Optical Waveguides Formed by Deuterium Passivation of Acceptors in Si Doped p-Type GaAs Epilayers", <u>J. Appl. Phys.</u> , Vol. 71, No. 9, pp. 4151-4155 (May 1, 1992).	

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